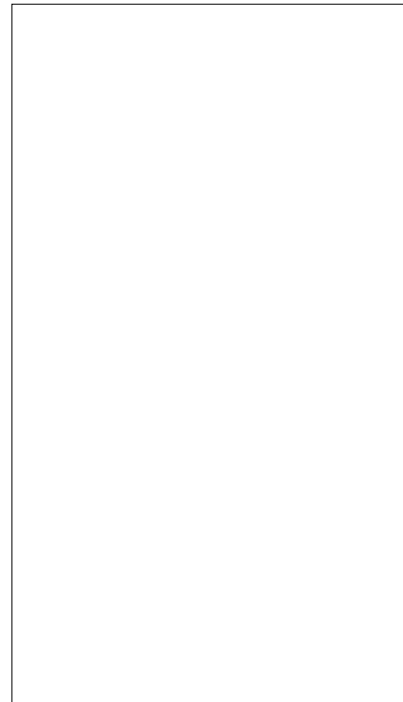




JCT616H 16A SCR

Rev.A.1.1

With high ability to withstand the shock loading of large current, JCT616H of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.

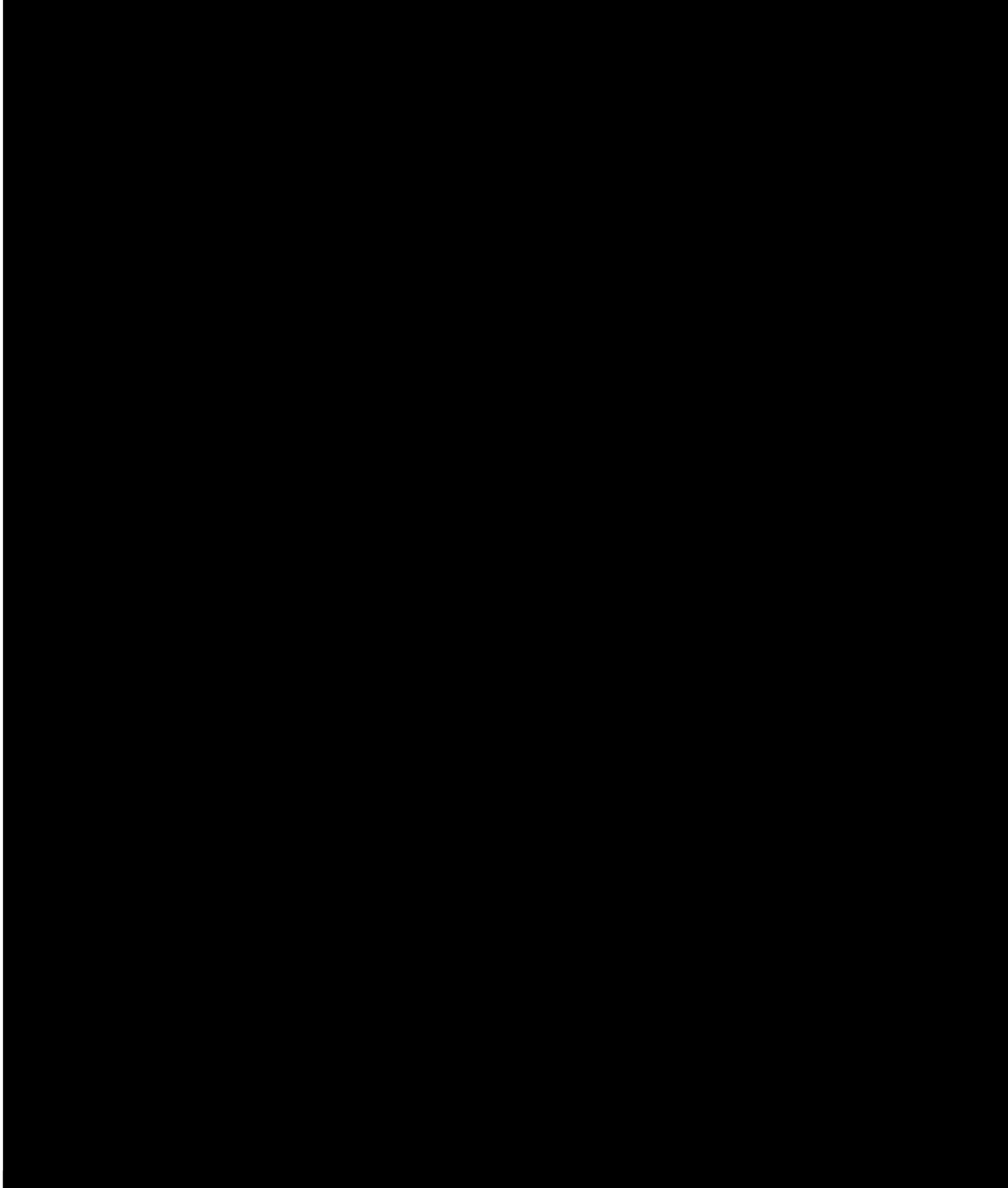


Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	

JCT616H

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
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CAL)5.2 CHARACTERISTICS (TI)3(CS(ow)1 3 06 70.9cj EMC P<.49688 0 T2D [(W)10.56 70W2525Tw/B.04



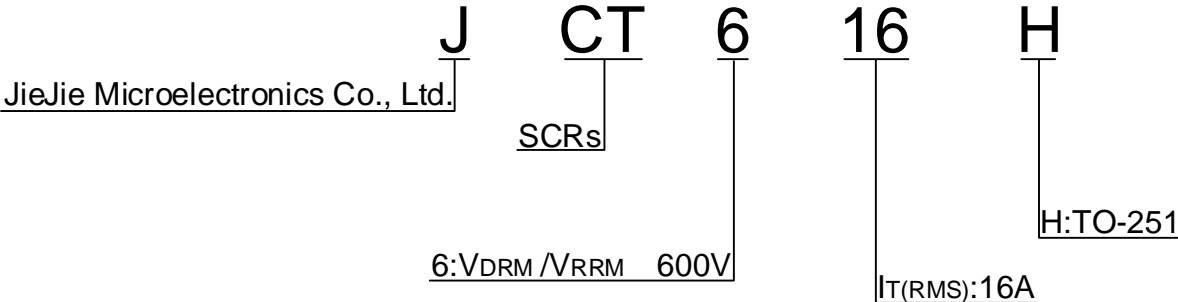


FIG.1: Maximum power dissipation versus RMS on-state current

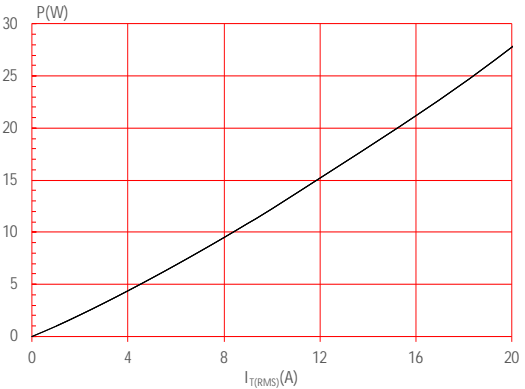
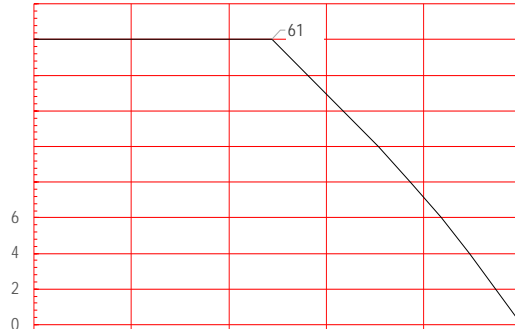


FIG.2: RMS on-state current versus case temperature



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT616H	600	15	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A. .0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

JCT616H

JieJie Microelectronics Co., Ltd.